Abstract

Novel copolymers suitable for forming the top layer photoimagable coating in a deep UV, particularly a 193nm and 248 nm, bilayer resist system providing high resolution photolithography. Chemically amplified photoresist composition and organosilicon moieties suitable for use in the binder resin for photoimagable etching resistant photoresist composition that is suitable as a material for use in ArF and KrF photolithography using the novel copolymers.